

CLAIM:

1. A method for recognizing and rectifying etch-critical regions, said method comprising the steps of accessing the data structure of a layout; accessing the data structure of the configuration elements arranged in a plane of the layout; and using the measures of a program procedure, determining the critical regions between the configuration elements, modifying the critical regions and visually displaying the modified critical regions.
2. A method according to claim 1, wherein the modifying of the critical regions is undertaken so that no under-etching can be formed, said modified critical regions being integrated into the existing data structure of the layout.
3. A method according to claim 1, wherein the determining of the critical regions is defined by height and spacing of the coating to be etched off.
4. A method according to claim 1, wherein the critical region is adjustable by an admissible, fabrication-oriented, minimal spacing between the configuration elements.
5. A method according to claim 4, wherein the critical regions between the configuration elements are filled out by polygons so that the critical regions between the configuration elements are avoided.
6. A method according to claim 5, wherein the polygons of the critical regions are limited given possible superimpositions of the configuration elements.
7. A method according to claim 6, wherein the polygons of the critical regions are enlarged slightly so that the edges of the polygons superimpose with the edges of the configuration elements.